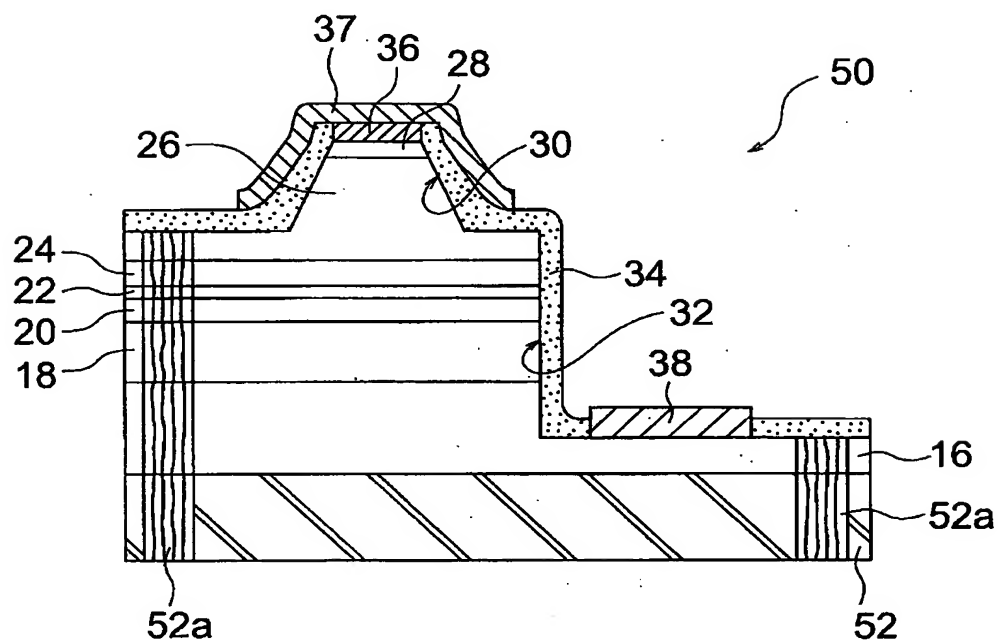


Fig.1A



(b)

Fig.1B

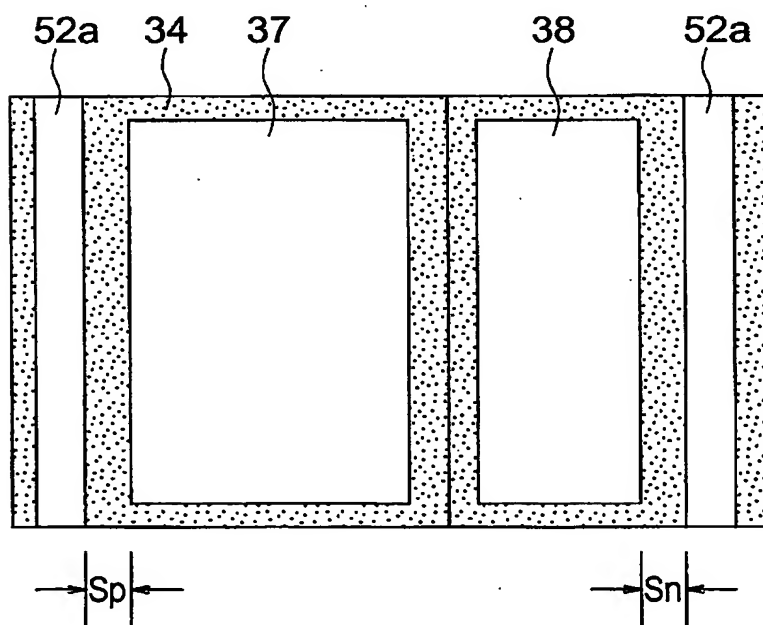


Fig.2A

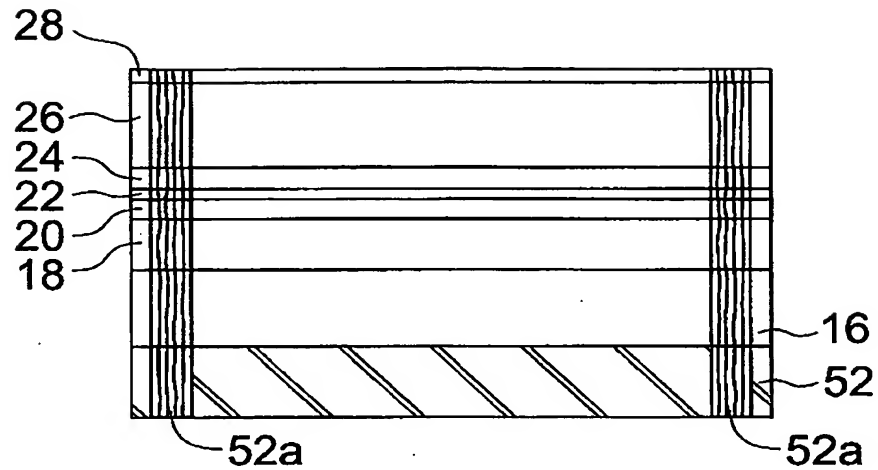


Fig.2B

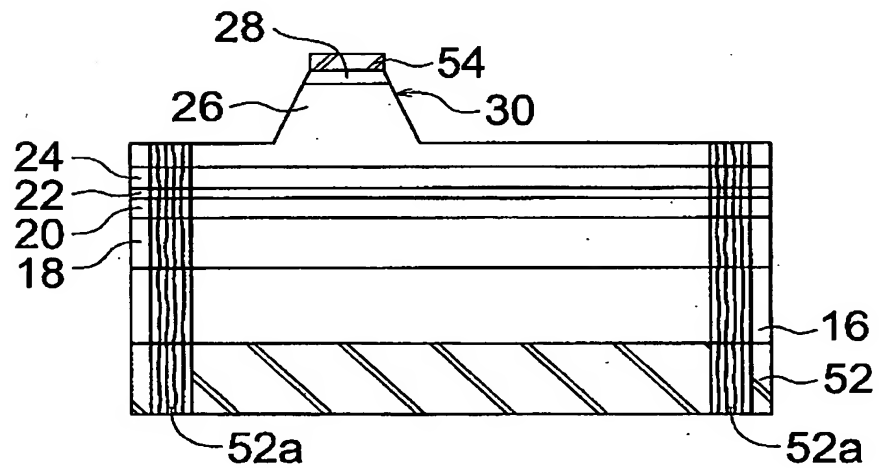


Fig.2C

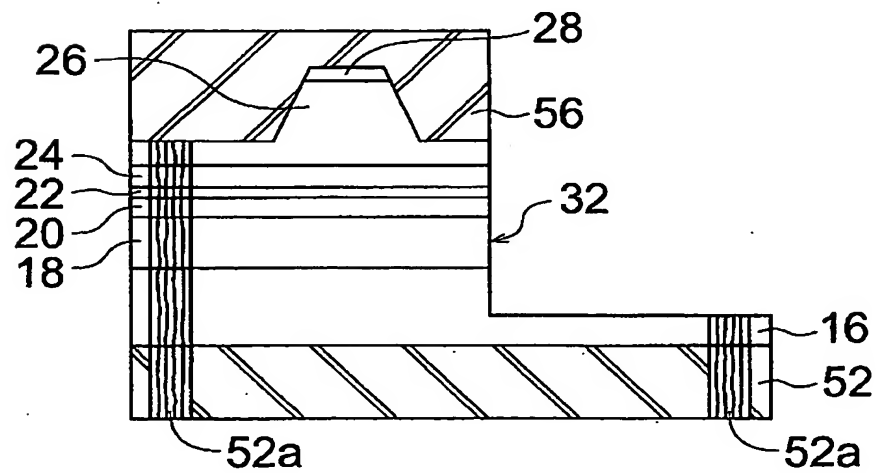


Fig.3A

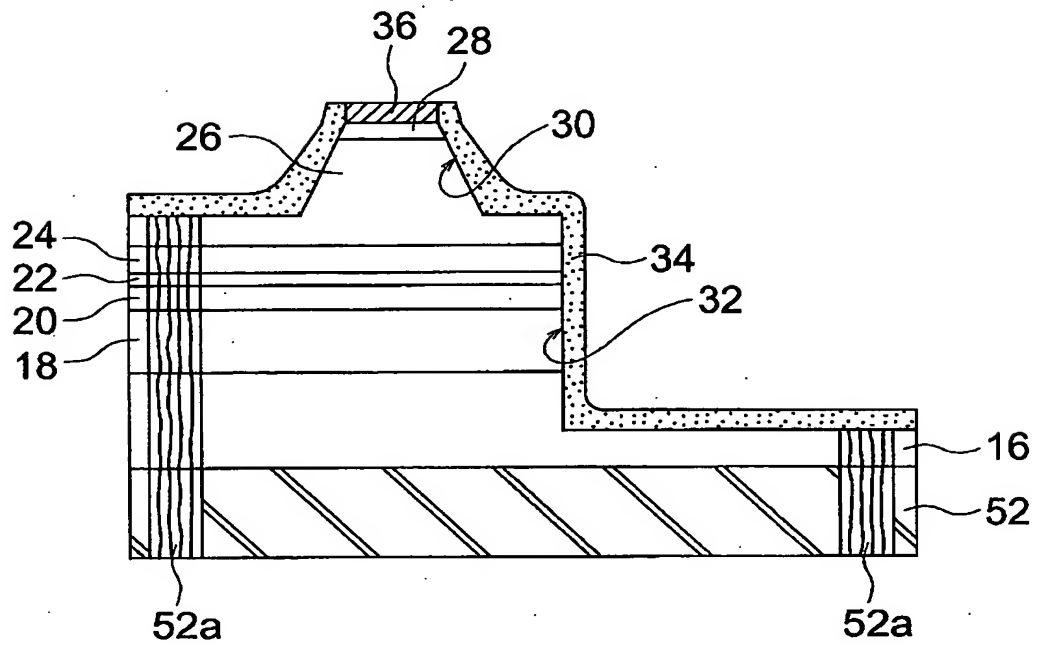


Fig.3B

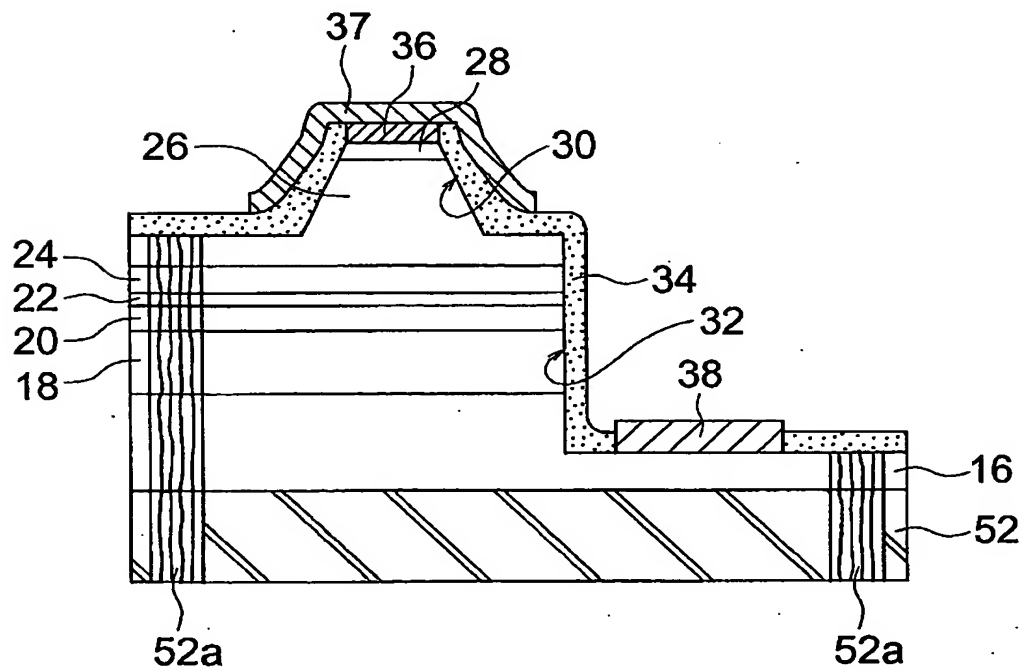


Fig.4A

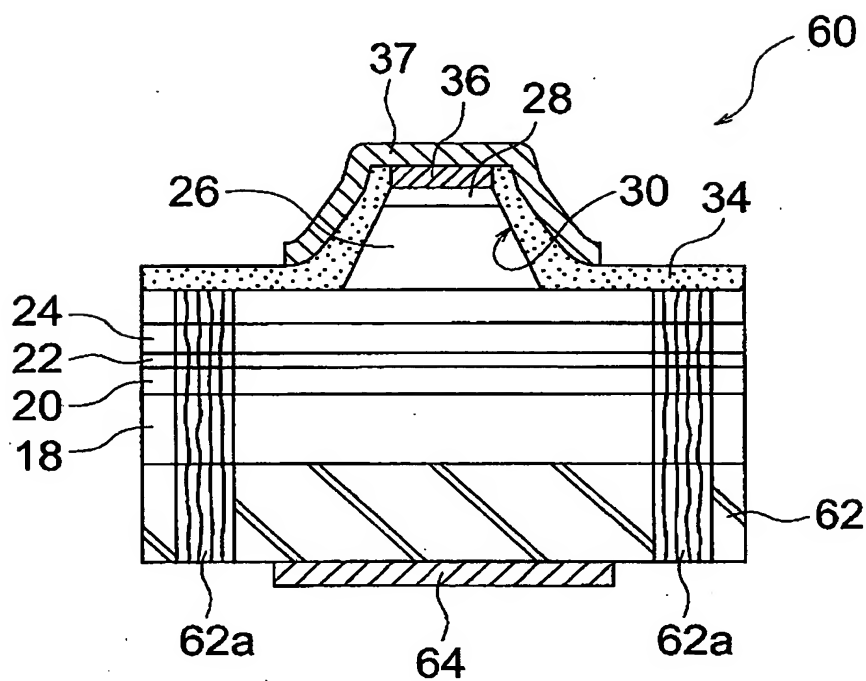
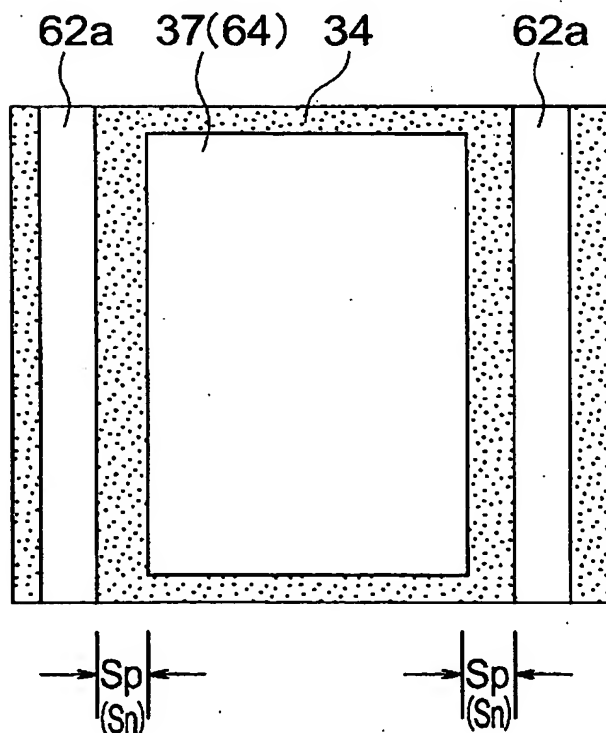


Fig.4B



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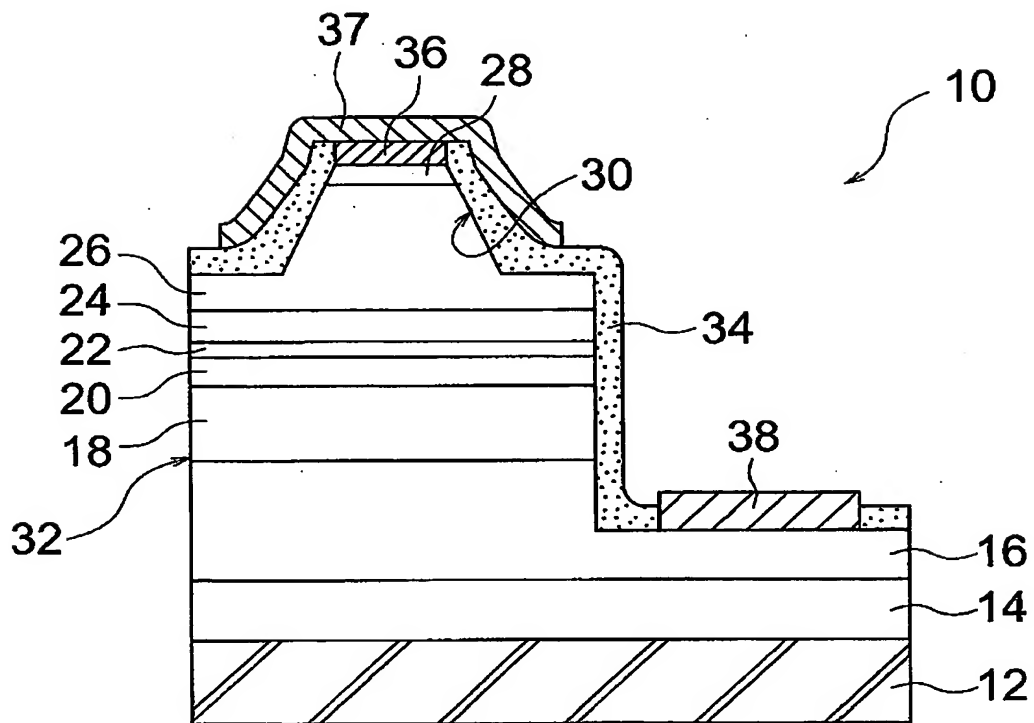


Fig.5

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Fig.6A

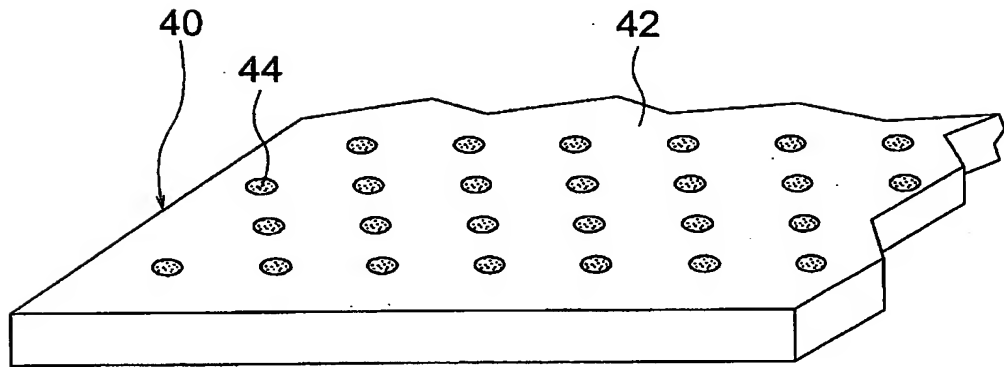
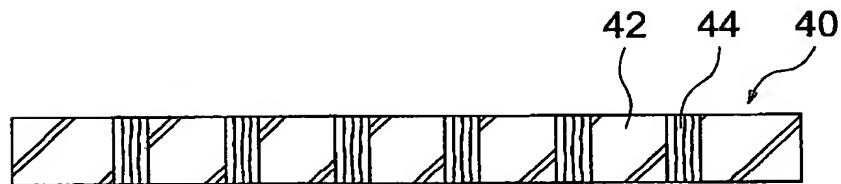


Fig.6B



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Fig. 7A

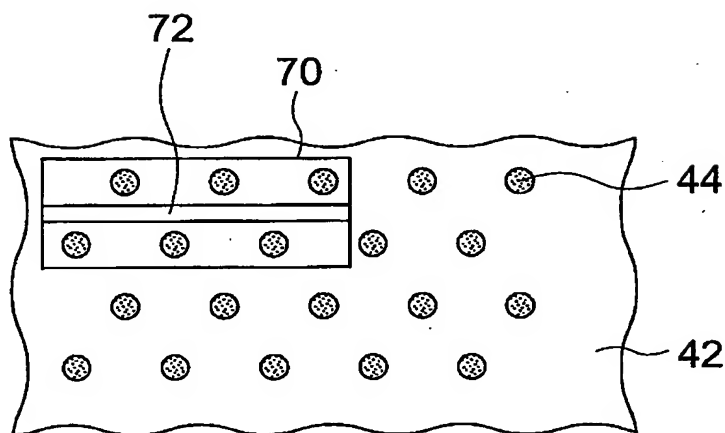


Fig. 7B

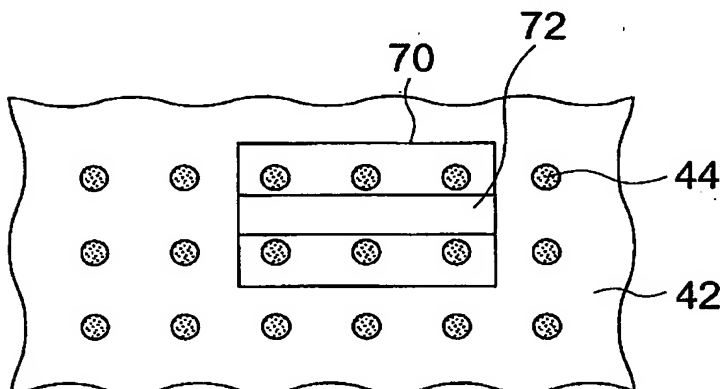
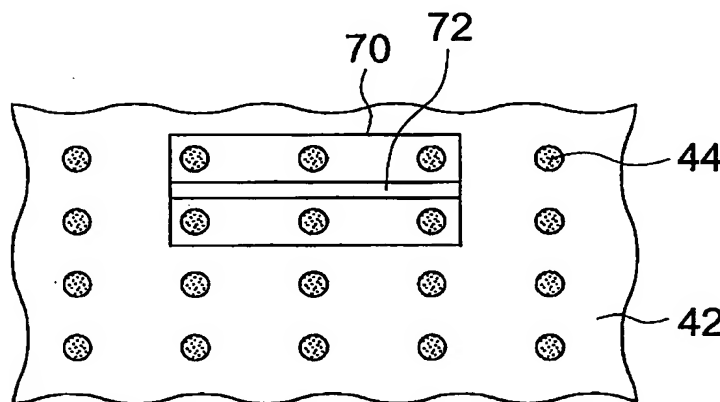


Fig. 7C



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Fig.8A

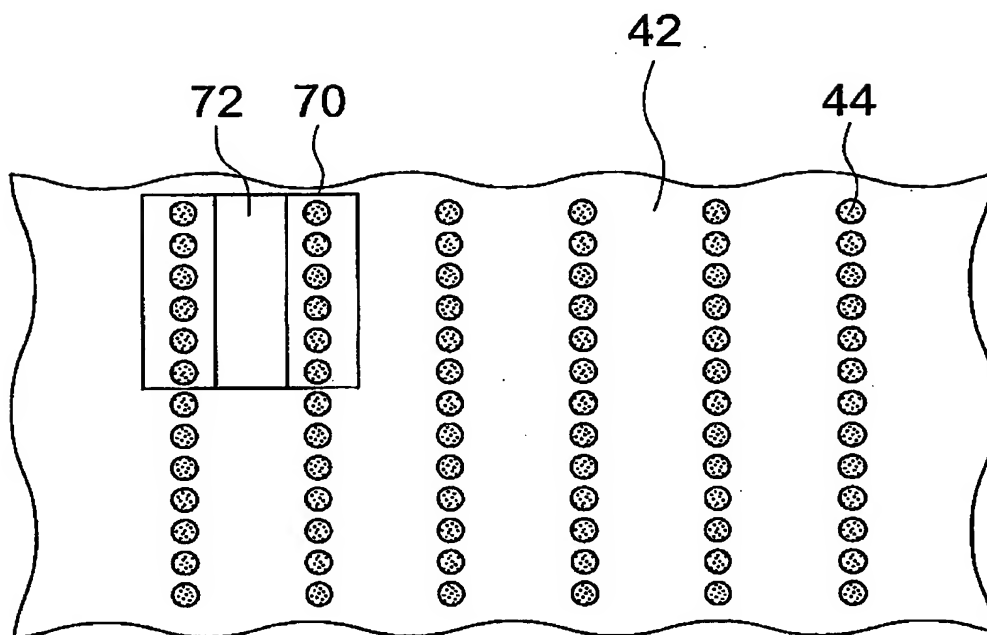
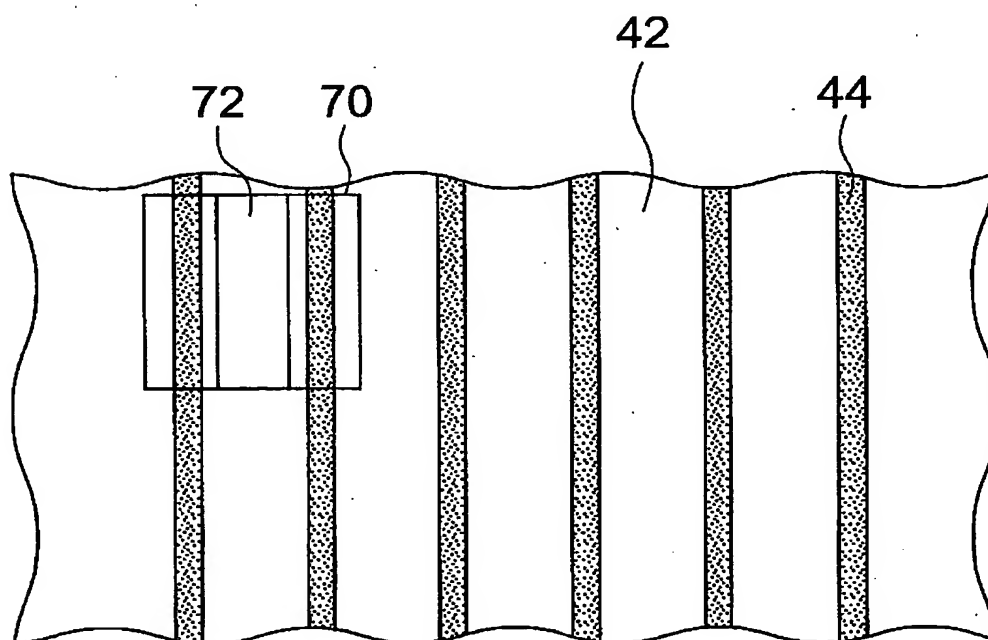


Fig.8B



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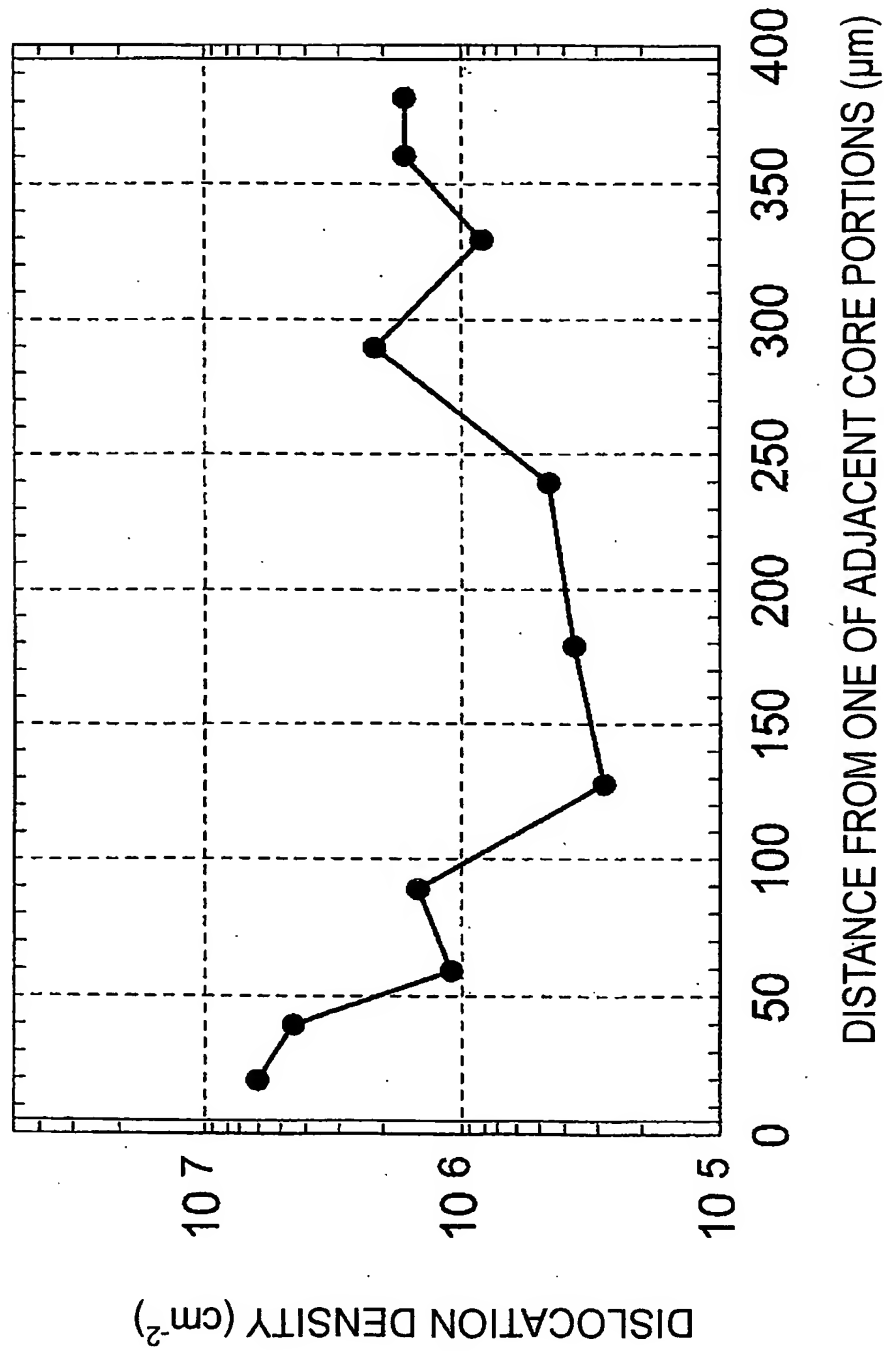


Fig.9

GaN-BASED SEMICONDUCTOR DEVICE
Inventor: Osamu Goto et al.
Attorney Docket No.: 075834.00402
Robert J. Depke, Holland & Knight LLC - (312) 263-3600

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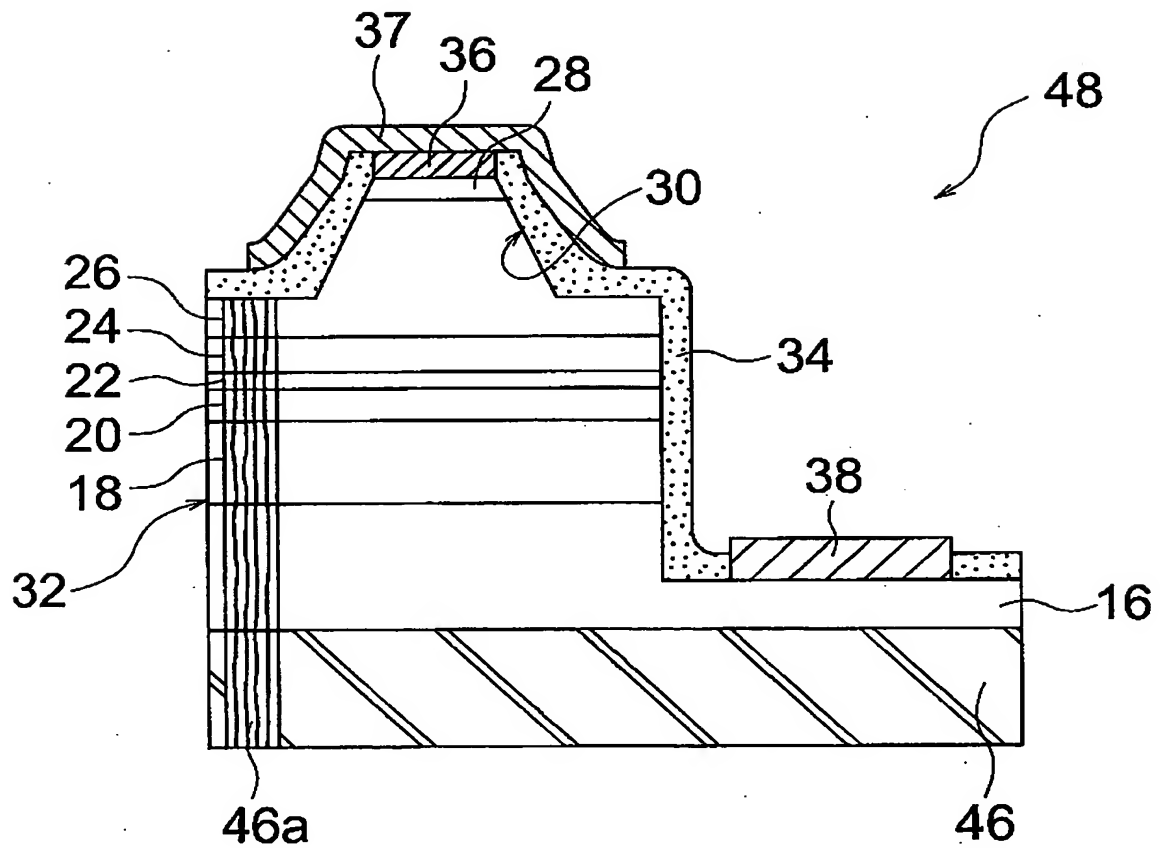


Fig.10

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Fig.11A

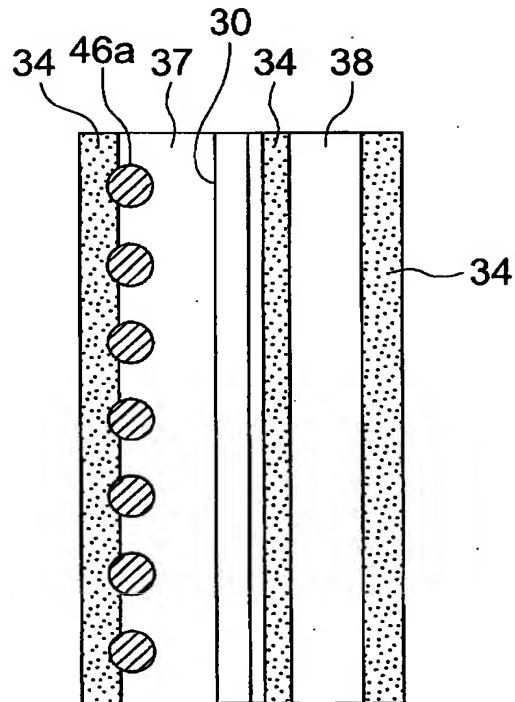
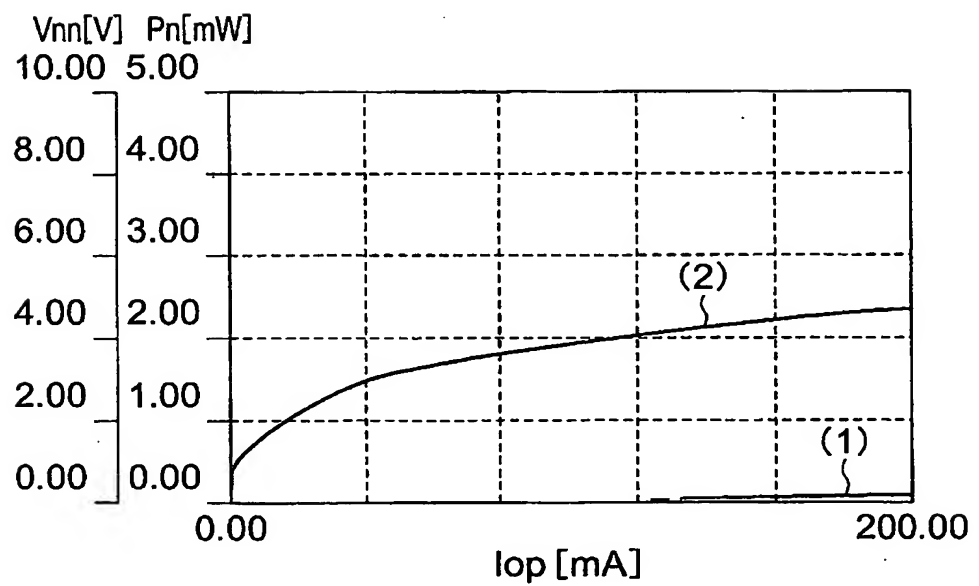


Fig.11B



GaN-BASED SEMICONDUCTOR DEVICE
Inventor: Osamu Goto et al.
Attorney Docket No.: 075834.00402
Robert J. Depke, Holland & Knight LLC - (312) 263-3600

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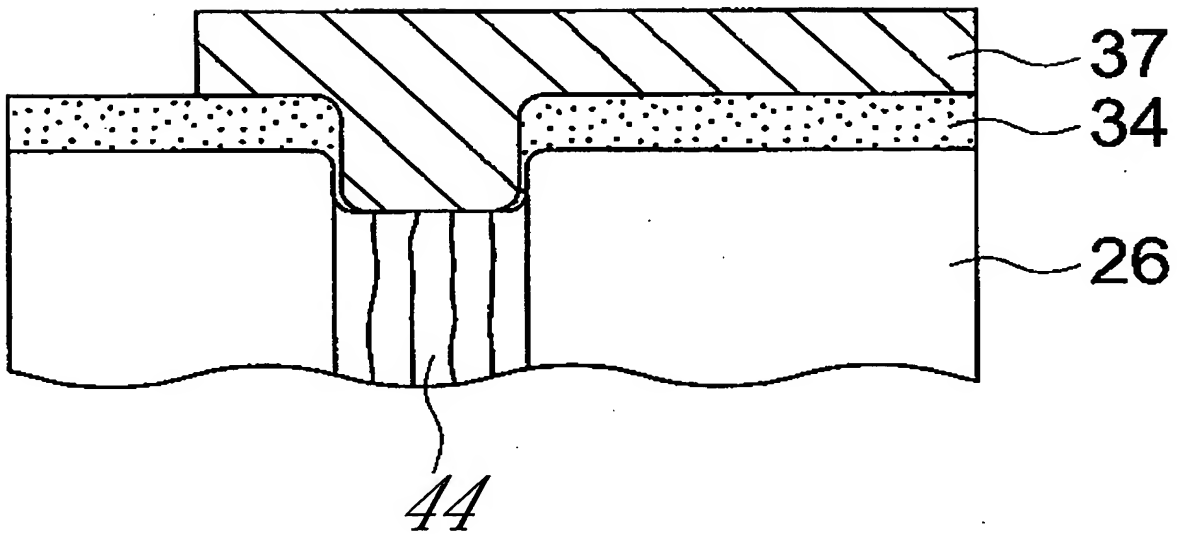


Fig.12

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Fig.13A

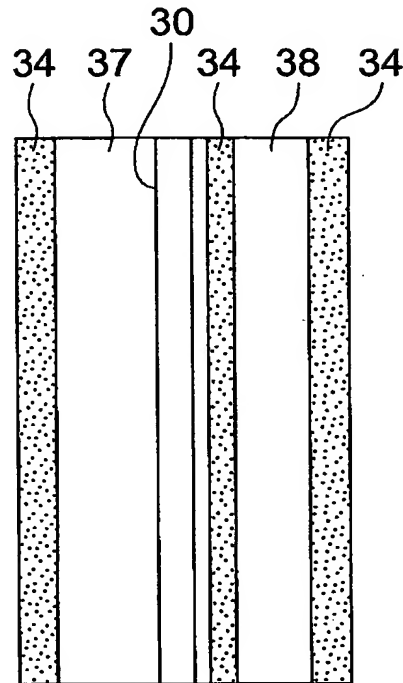


Fig.13B

